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SEMICONDUCTOR®

November 2013

FQB6N80

N-Channel QFET® MOSFET

800 V, 5.8 A, 1.95 Ω

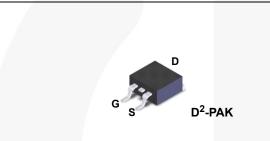
Description

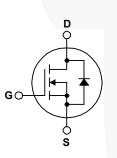
This N-Channel enhancement mode power MOSFET is • 5.8 A, 800 V, $R_{DS(on)}$ = 1.95 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state D = 2.9 A Low Gate Charge (Typ. 31 nC) resistance, and to provide superior switching performance . Low Crss (Typ. 14 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_{D} = 2.9 A$

- · RoHS Compiant





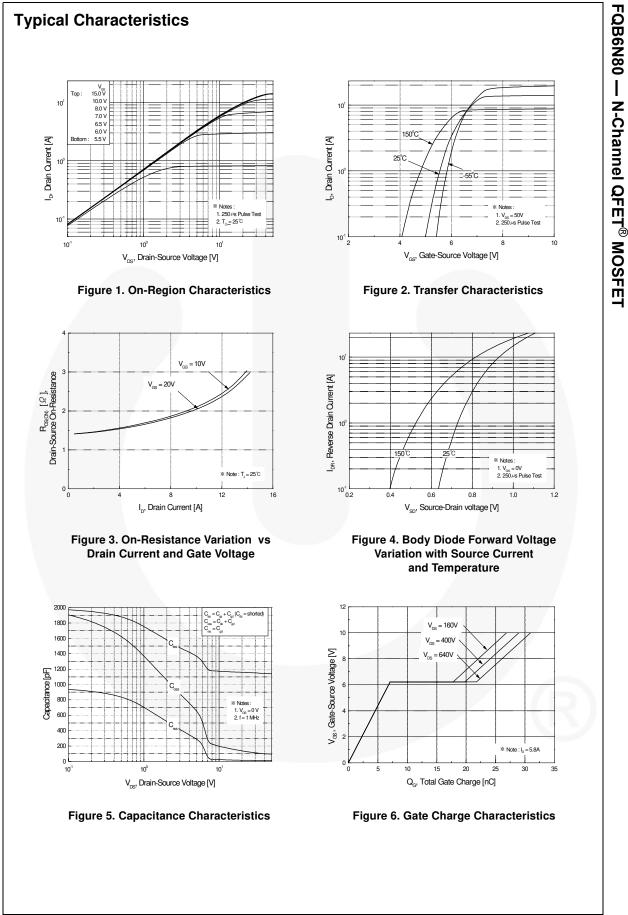
Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

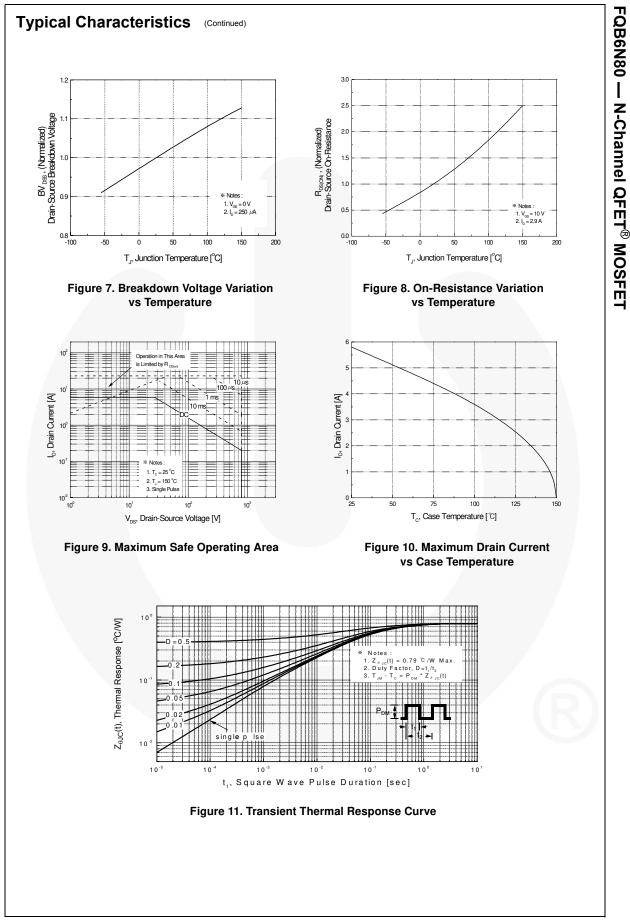
Symbol	Parameter		FQB6N80TM	Unit
V _{DSS}	Drain-Source Voltage		800	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		5.8	А
	- Continuous (T _C = 100°C)		3.67	A
I _{DM}	Drain Current - Pulsed	(Note 1)	23.2	A
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	680	mJ
I _{AR}	Avalanche Current	(Note 1)	5.8	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	15.8	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.0	V/ns
P _D	Power Dissipation $(T_A = 25^{\circ}C)^{*}$		3.13	W
	Power Dissipation ($T_C = 25^{\circ}C$)		158	W
	- Derate above 25°C		1.27	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
ΤL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C

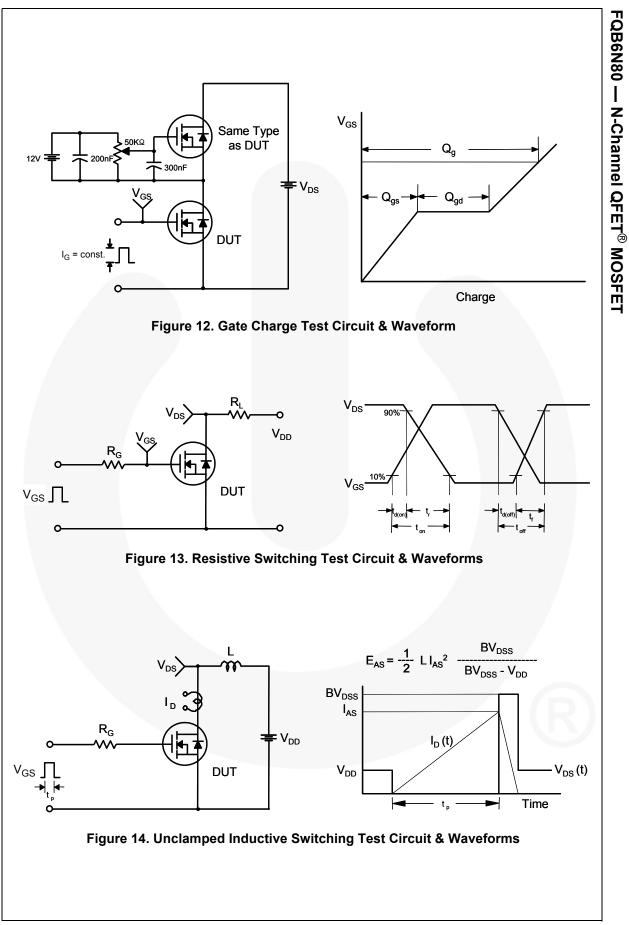
Thermal Characteristics

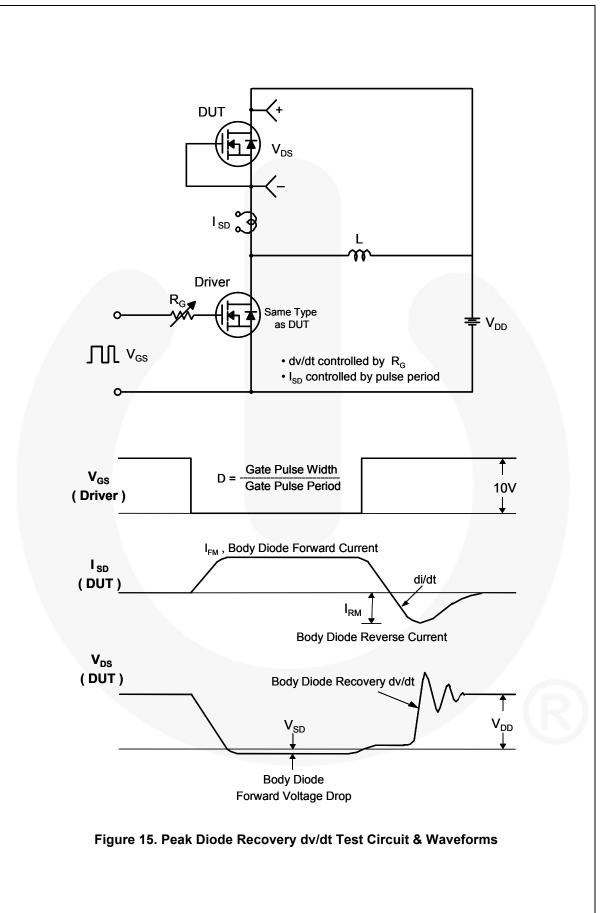
Symbol	Parameter	FQB6N80TM	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.79	
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40	

Part Number Top Mark Pac			Pack	kage Packing Method Reel		Size	Tape Width		Quantity		
FQB6N80TM FQB6N80 D ² -		D ² -I	PAK Tape and Reel 330			330	mm	24 m	n	800 units	
loctrid	cal Cha	racteristics									
Symbol		Parameter	1 _C = 25°0	J unless of	herwise noted. Test Conc	litions		Min.	Тур.	Мах	. Unit
					1001 0011					mux	
Off Cha BV _{DSS}	aracterist		000	Vee =	$0 \sqrt{1} = 25$	۵ ۵		800			V
∆BV _{DSS}		Drain-Source Breakdown Voltage			V _{GS} = 0 V, I _D = 250 μA			000			v
$/\Delta T_{J}$		Breakdown Voltage Temperature Coefficient		I_D = 250 µA, Referenced to 25°C				0.9		V/°C	
I _{DSS}	Zero Gate	Voltage Drain Curr	$V_{DS} = 640 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$		V _{DS} = 800 V, V _{GS} = 0 V					10	μA
		•					100	μA			
I _{GSSF}		/ Leakage Current,			30 V, V _{DS} =					100	nA
I _{GSSR}	Gate-Body	/ Leakage Current,	Reverse	V _{GS} =	-30 V, V _{DS} =	= 0 V				-100	nA
On Cha	aracterist	ics									
V _{GS(th)}	Gate Thre	shold Voltage	-	V _{DS} =	V _{GS} , I _D = 25	60 μA	- /	3.0		5.0	V
R _{DS(on)}	Static Drai On-Resist			$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2.9 \text{ A}$				1.5	1.95	Ω	
9 _{FS}	Forward T	ransconductance		V _{DS} =	50 V, I _D = 2.	9 A			5.9		S
Dynam	ic Charac	toristics		•							
C _{iss}	Input Capa		-	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz				1150	1500	pF	
C _{oss}	Output Ca		_					125	160	pF	
C _{rss}	Reverse T	ransfer Capacitance	е		1 - 1.0 WHZ				14	18	pF
Cultab	ing Char										
	Turn-On D	acteristics	-	1					30	70	ns
t _r	Turn-On R		_		$V_{DD} = 400 \text{ V}, \text{ I}_{D} = 5.8 \text{ A},$				70	150	ns
t _{d(off)}	Turn-Off D		-	_ R _G = 25 Ω					65	140	ns
t _f	Turn-Off F	,	-			(Note 4)			45	100	ns
Q _g	Total Gate Charge		$V_{-} = 640 V_{-} = 5.8 A$				31	100	nC		
Q _{gs}		ce Charge		$V_{DS} = 640 \text{ V}, \text{ I}_{D} = 5.8 \text{ A},$ $V_{GS} = 10 \text{ V}$					7.1		nC
Q _{gd}	Gate-Drai	Ū		(Note 4)					15		nC
		Ŭ									
	T	ode Characteri Continuous Drain-S								5.8	A
l _S									23.2		
I _{SM} V _{SD}	Maximum Pulsed Drain-Source Diode F Drain-Source Diode Forward Voltage			$V_{GS} = 0 V, I_S = 5.8 A$					1.4	V	
		Recovery Time	vollage					650		-	
t _{rr} Q _{rr}		Recovery Charge		$V_{GS} = 0 V, I_S = 5.8 A,$ $dI_F / dt = 100 A/\mu s$				5.7		ns µC	
. L = 38 mH, . I _{SD} ≤ 5.8 A	$I_{AS} = 5.8 \text{ A}, V_{DI}$ A, di/dt $\leq 200 \text{ A}$	th limited by maximum junction $_{D}$ = 50 V, R _G = 25 Ω , starti /µs , V _{DD} \leq BV _{DSS} , starti poperating temperature.	ng T _J = 25°0) .							R









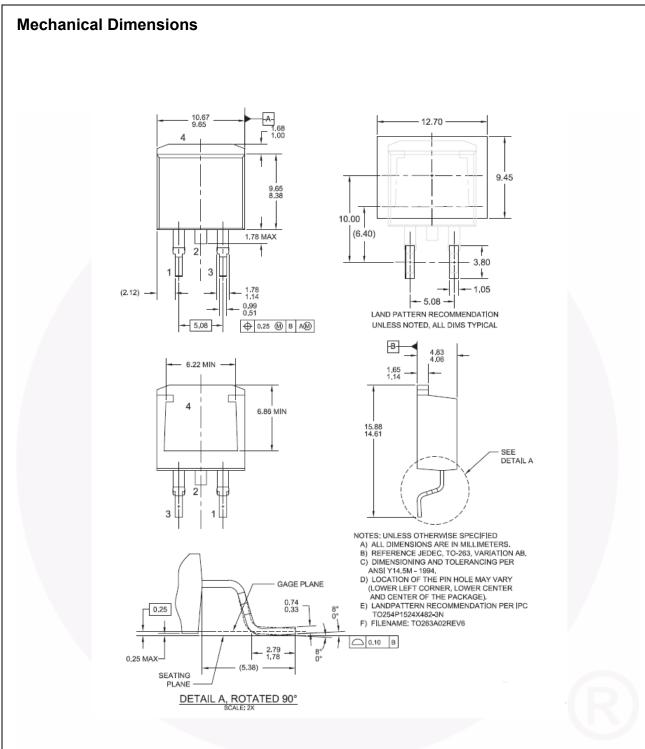


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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FQB6N80 — N-Channel QFET[®] MOSFET



	Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
_	Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
	No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
	Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.
			Rev. 166

QB6N80

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N-Channel QFET[®] MOSFET

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